风光欣技术资料

C3195

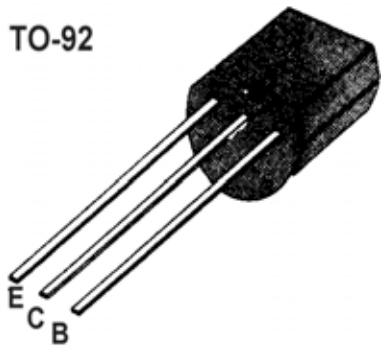
—NPN silicon —

■■**APPLICATION:** **POWER AMPLIFIER APPLICATION、**

SWITCHING APPLICATION.

■■**MAXIMUM RATINGS**（Ta＝25℃）

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V_{CBO}	40	V
Collector-emitter voltage	V_{CEO}	30	V
Emitter-base voltage	V_{EBO}	4	V
Collector current	I_C	20	mA
Collector Power Dissipation	P_C	400	mW
Junction Temperature	T_J	150	℃
Storage Temperature Range	Tstg	－55~150	℃



■■ **ELECTRICAL CHARACTERISTICS**（Ta=25℃）

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h_{FE}	40		200		V_{CE}= 6V，Ic= 1mA
Collector Cut-off Current	I_{CBO}			0.5	μA	V_{CB}= 40V，I_E=0
Emitter Cut-off Current	I_{EBO}			0.5	μA	V_{EB}= 4V，Ic=0
Collector-Base Breakdown Voltage	BV_{CBO}	40			V	Ic= 0.1mA，I_E=0
Collector-Emitter Breakdown Voltage	BV_{CEO}	30			V	Ic= 1mA，I_B=0
Emitter-Base Breakdown Voltage	BV_{EBO}	4			V	I_E= 0.1mA，Ic=0
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			0.2	V	Ic= 15mA，I_B= 1.5mA
Gain bandwidth product	f_T		550		MHz	Ic= 1mA，V_{CE}= 6V
Common Base Output Capacitance	Cob		0.7		PF	V_{CB}= 6V, I_E=0, f = 1MHz
Power Gain	G_P		18		dB	V_{CE}= 6V,I_E= -1mA,f= 100MHz
Noise Figure	N_F		2.5	5.0	dB	V_{CE}= 6V,I_E= -1mA,f= 100MHz

■■h_{FE} **Classification**

Classification	R	O	Y
h_{FE}	40~80	70~140	100~200